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PMEG6030ETP

High-temperature 60 V, 3 A Schottky barrier rectifier

15 October 2012

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Average forward current: $I_{F(AV)} \leq 3$ A
- Reverse voltage: $V_R \leq 60$ V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature $T_j \leq 175$ °C

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_F	forward current	$T_{sp} = 160$ °C		-	-	4.2	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20$ kHz; $T_{amb} \leq 80$ °C; square wave	[1]	-	-	3	A
		$\delta = 0.5$; $f = 20$ kHz; $T_{sp} \leq 165$ °C; square wave		-	-	3	A
V_R	reverse voltage	$T_j = 25$ °C		-	-	60	V
V_F	forward voltage	$I_F = 3$ A; $T_j = 25$ °C		-	460	530	mV
I_R	reverse current	$T_j = 25$ °C; $V_R = 60$ V; $t_p \leq 300$ μ s; $\delta \leq 0.02$; pulsed		-	80	200	μ A



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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{rr}	reverse recovery time	$I_R = 0.5\text{ A}$; $I_F = 0.5\text{ A}$; $I_{R(meas)} = 0.1\text{ A}$; $T_J = 25\text{ °C}$	-	12	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al_2O_3 , standard footprint.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	 SOD128	 sym001
2	A	anode		

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG6030ETP	SOD128	plastic surface-mounted package; 2 leads	SOD128

4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6030ETP	DA

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage	$T_J = 25\text{ °C}$	-	60	V
I_F	forward current	$T_{sp} = 160\text{ °C}$	-	4.2	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{amb} \leq 80\text{ °C}$; square wave	[1]	3	A
		$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{sp} \leq 165\text{ °C}$; square wave	-	3	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$; $T_{j(init)} = 25\text{ °C}$; square wave	-	50	A

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Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25\text{ }^{\circ}\text{C}$	[2]	-	750	mW
			[3]	-	1250	mW
			[1]	-	2500	mW
T_j	junction temperature			-	175	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	175	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	175	$^{\circ}\text{C}$

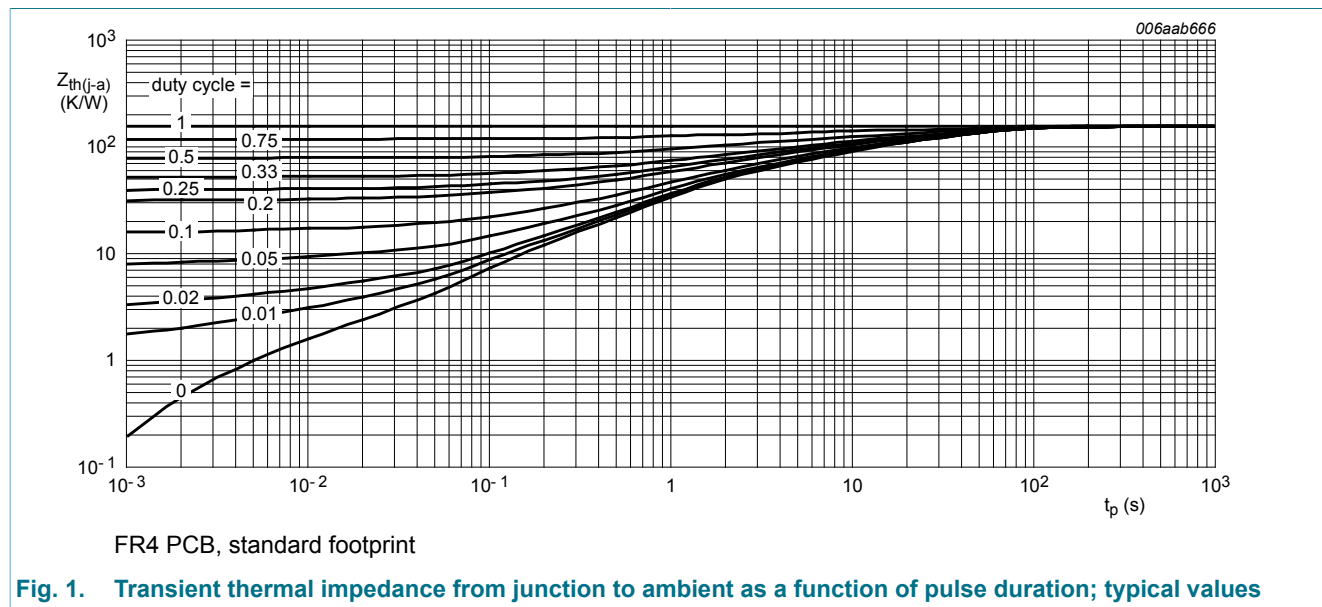
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al_2O_3 , standard footprint.
 [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
 [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	200	K/W
			[1][3]	-	-	120	K/W
			[1][4]	-	-	60	K/W
$R_{\text{th(j-sp)}}$	thermal resistance from junction to solder point		[5]	-	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
 [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
 [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .
 [4] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.
 [5] Soldering point of cathode tab.



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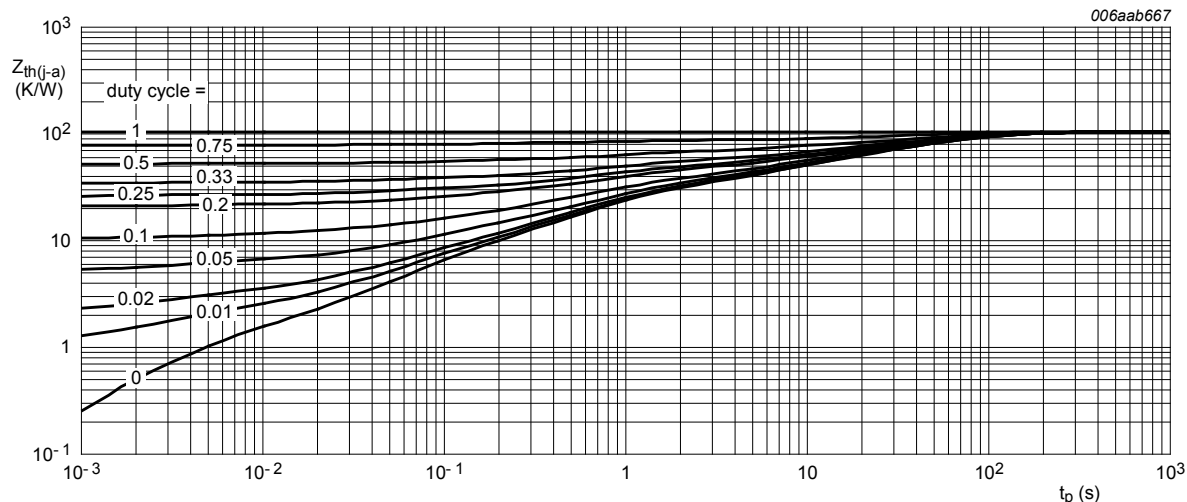


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

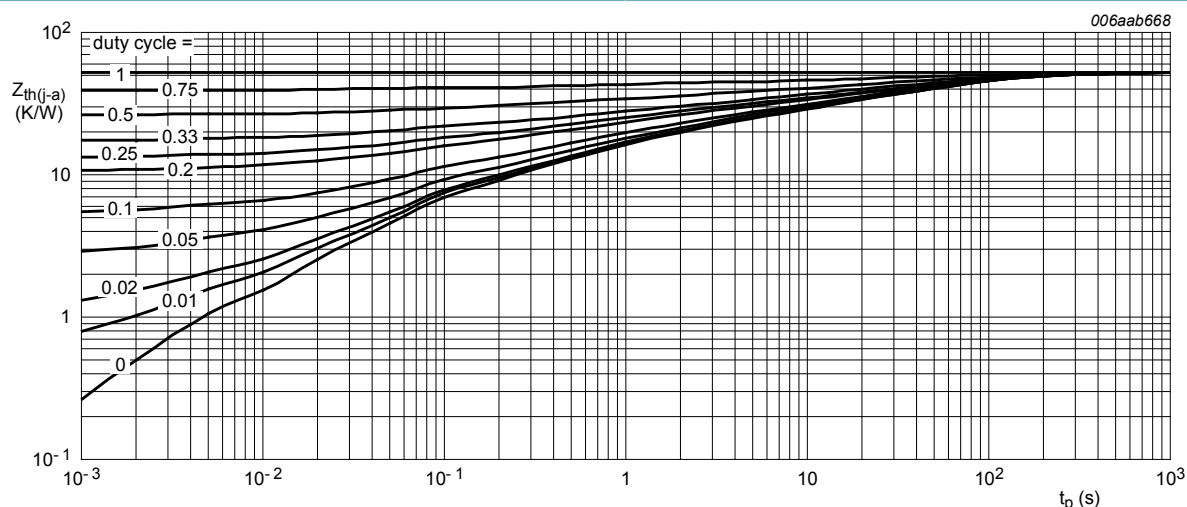


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _F	forward voltage	I _F = 0.1 A; T _j = 25 °C	-	290	330	mV
		I _F = 0.5 A; T _j = 25 °C	-	340	400	mV
		I _F = 1 A; T _j = 25 °C	-	380	440	mV
		I _F = 1.5 A; T _j = 25 °C	-	400	470	mV
		I _F = 2 A; T _j = 25 °C	-	430	500	mV
		I _F = 3 A; T _j = 25 °C	-	460	530	mV

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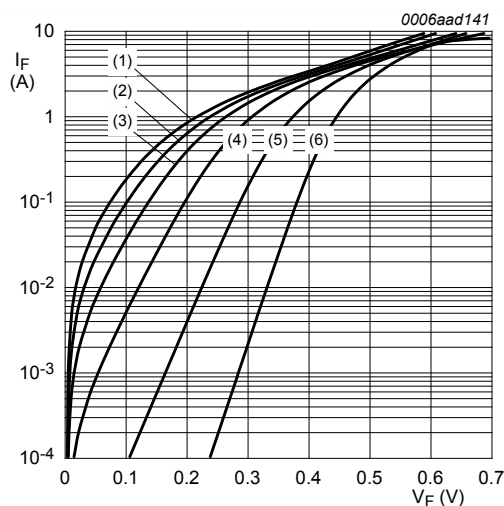
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$I_F = 3 \text{ A}; T_J = -40 \text{ }^{\circ}\text{C}$	-	510	590	mV
		$I_F = 3 \text{ A}; T_J = 125 \text{ }^{\circ}\text{C}$	-	405	480	mV
		$I_F = 3 \text{ A}; T_J = 150 \text{ }^{\circ}\text{C}$	-	390	460	mV
		$I_F = 3 \text{ A}; T_J = 175 \text{ }^{\circ}\text{C}$	-	370	450	mV
I_R	reverse current	$V_R = 5 \text{ V}; T_J = 25 \text{ }^{\circ}\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$; pulsed	-	4	-	μA
		$V_R = 10 \text{ V}; T_J = 25 \text{ }^{\circ}\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$; pulsed	-	5	-	μA
		$V_R = 60 \text{ V}; T_J = 25 \text{ }^{\circ}\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$; pulsed	-	80	200	μA
		$V_R = 60 \text{ V}; T_J = -40 \text{ }^{\circ}\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$; pulsed	-	0.5	10	μA
		$V_R = 60 \text{ V}; T_J = 125 \text{ }^{\circ}\text{C}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02$; pulsed	-	45	150	mA
C_d	diode capacitance	$V_R = 1 \text{ V}; f = 1 \text{ MHz}; T_J = 25 \text{ }^{\circ}\text{C}$	-	360	-	pF
		$V_R = 10 \text{ V}; f = 1 \text{ MHz}; T_J = 25 \text{ }^{\circ}\text{C}$	-	120	-	pF
t_{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(\text{meas})} = 0.1 \text{ A}; T_J = 25 \text{ }^{\circ}\text{C}$	-	12	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 40 \text{ A}/\mu\text{s}; T_J = 25 \text{ }^{\circ}\text{C}$	-	425	-	mV

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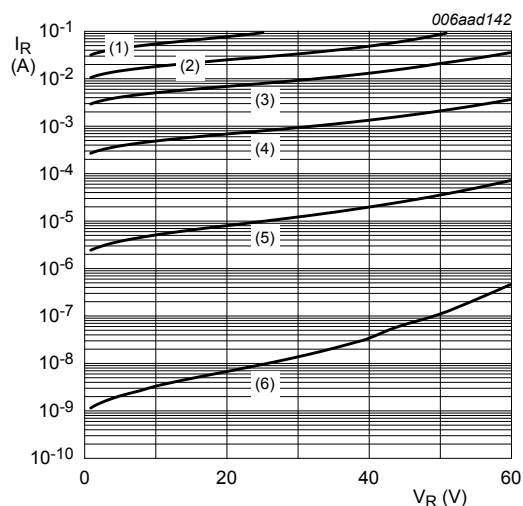
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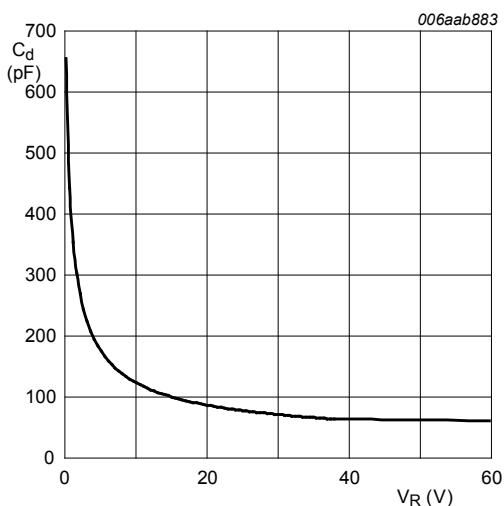
- (1) $T_j = 175\text{ °C}$
- (2) $T_j = 150\text{ °C}$
- (3) $T_j = 125\text{ °C}$
- (4) $T_j = 85\text{ °C}$
- (5) $T_j = 25\text{ °C}$
- (6) $T_j = -40\text{ °C}$

Fig. 4. Forward current as a function of forward voltage; typical values



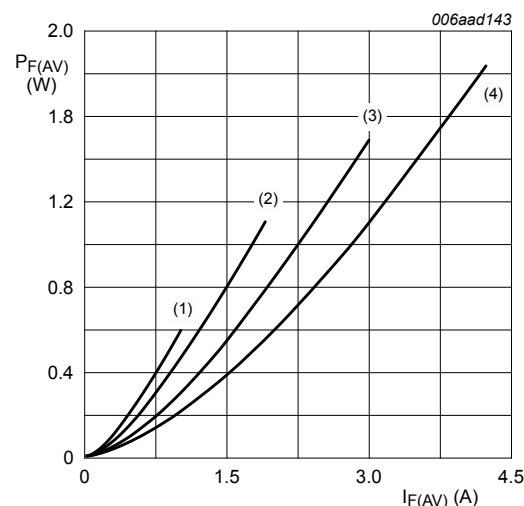
- (1) $T_j = 175\text{ °C}$
- (2) $T_j = 150\text{ °C}$
- (3) $T_j = 125\text{ °C}$
- (4) $T_j = 85\text{ °C}$
- (5) $T_j = 25\text{ °C}$
- (6) $T_j = -40\text{ °C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}$; $T_{amb} = 25\text{ °C}$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



$T_j = 175\text{ °C}$

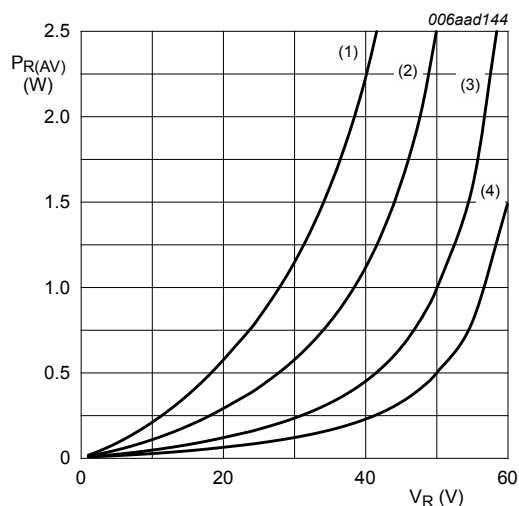
- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

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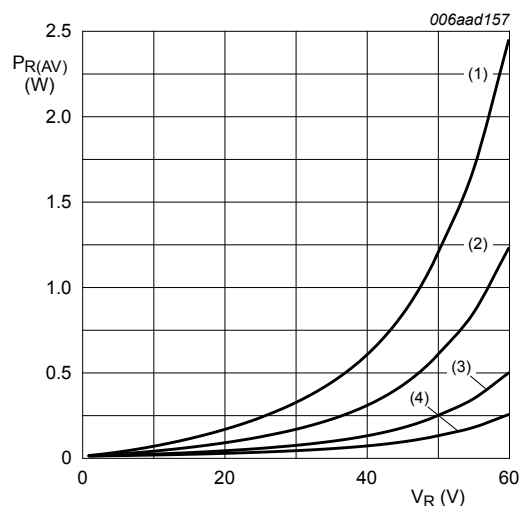
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$T_j = 150^\circ\text{C}$

- (1) $\delta = 1$
- (2) $\delta = 0.5$
- (3) $\delta = 0.2$
- (4) $\delta = 0.1$

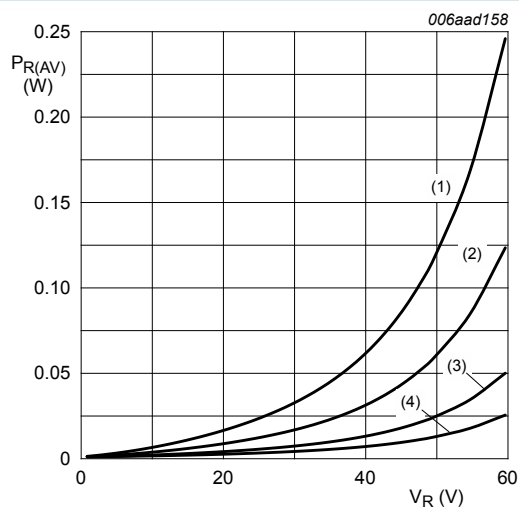
Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



$T_j = 125^\circ\text{C}$

- (1) $\delta = 1$
- (2) $\delta = 0.5$
- (3) $\delta = 0.2$
- (4) $\delta = 0.1$

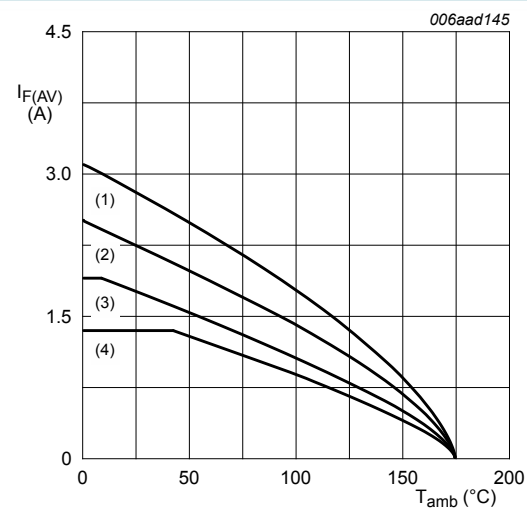
Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



$T_j = 85^\circ\text{C}$

- (1) $\delta = 1$
- (2) $\delta = 0.5$
- (3) $\delta = 0.2$
- (4) $\delta = 0.1$

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

$T_j = 175^\circ\text{C}$

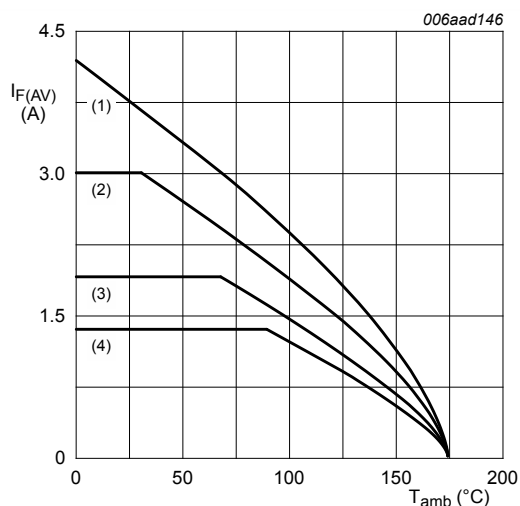
- (1) $\delta = 1$ (DC)
- (2) $\delta = 0.5$; $f = 20$ kHz
- (3) $\delta = 0.2$; $f = 20$ kHz
- (4) $\delta = 0.1$; $f = 20$ kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values

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FR4 PCB, mounting pad for cathode 1 cm²

$T_j = 175\text{ °C}$

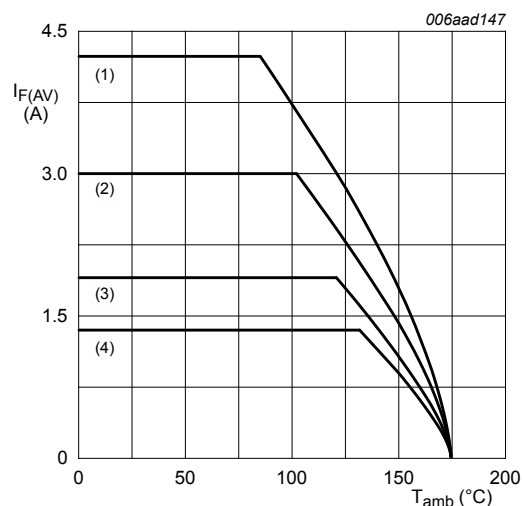
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

$T_j = 175\text{ °C}$

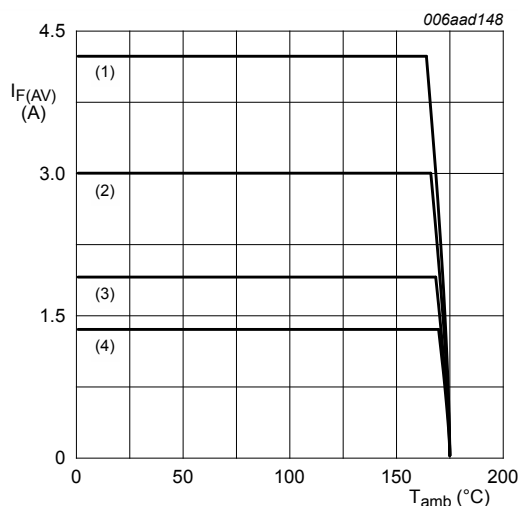
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 13. Average forward current as a function of ambient temperature; typical values



$T_j = 175\text{ °C}$

(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 14. Average forward current as a function of solder point temperature; typical values

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8. Test information

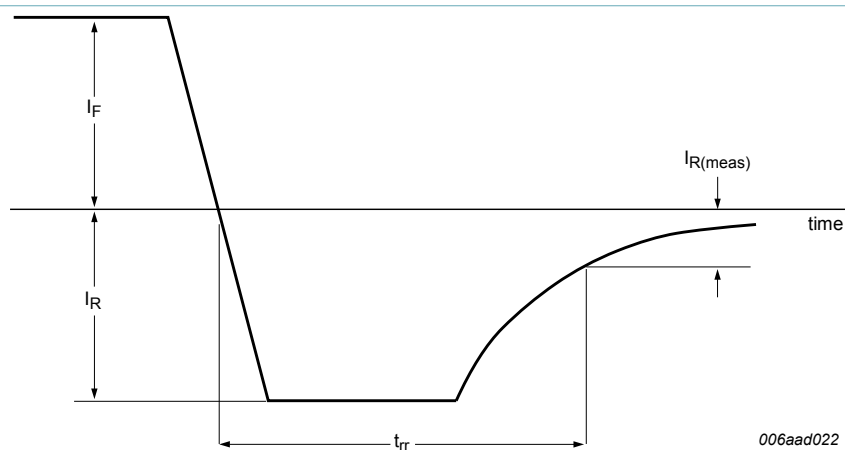


Fig. 15. Reverse recovery definition

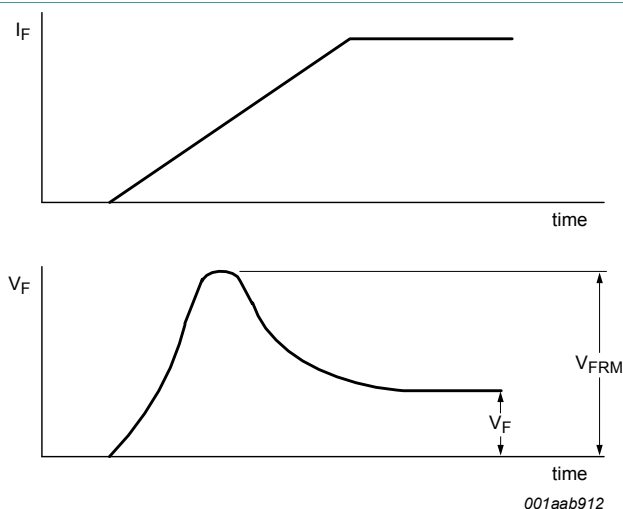


Fig. 16. Forward recovery definition

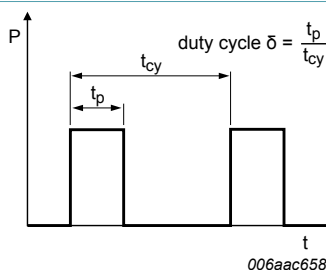


Fig. 17. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations:
 $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

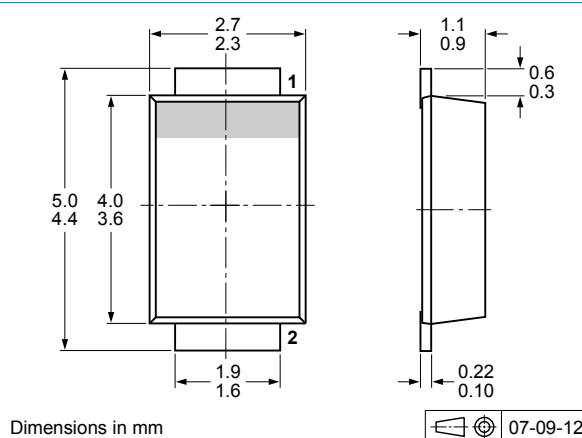


Fig. 18. Package outline SOD128

10. Soldering

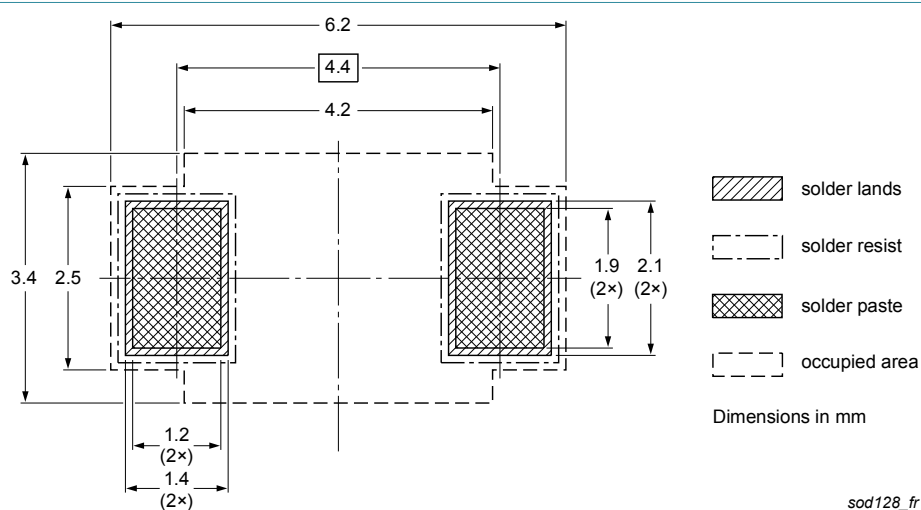


Fig. 19. Reflow soldering footprint for SOD128

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11. PMEG6030ETP

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6030ETP v.1	20121015	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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